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Diodes Incorporated DMN65D8LFB-7B

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Datasheet of DMN65D8LFB-7B - MOSFET N-CH 60V 260MA 3DFN

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DMN65D8LFB

N-CHANNEL ENHANCEMENT MODE FIELD MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)}	I _D T _A = +25°C
901/	3.0Ω @ V _{GS} = 10V	400mA
60V	4.0Ω @ V _{GS} = 5V	330mA

Features and Benefits

- N-Channel MOSFET
- Low On-Resistance
- Low Gate-Threshold Voltage
- Low-Input Capacitance
- · Fast Switching Speed
- Small-Surface Mount Package
- ESD Protected Gate, 1.2kV HBM
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

- DC-DC Converters
- Power Management Functions
- Battery Operated Systems and Solid-State Relays
 Drivers: Relays, Solenoids, Lamps, Hammers, Displays,
 Memories, Transistors, etc.

Mechanical Data

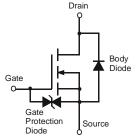
- Case: X1-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound;
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish NiPdAu over Copper Leadframe;
 Solderable per MIL-STD-202, Method 208 4
- Weight: 0.001 grams (Approximate)



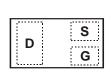




Bottom View



Equivalent Circuit



Top View Pin Configuration

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN65D8LFB-7	X1-DFN1006-3	3,000/Tape & Reel
DMN65D8LFB-7B	X1-DFN1006-3	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com.

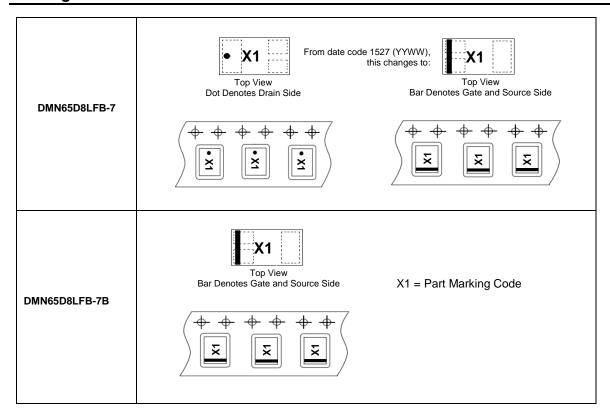
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Marking Information



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Maximum Ratings

Characteristic	Symbol	Value	Units		
Drain-Source Voltage	V_{DSS}	60	V		
Gate-Source Voltage	V_{GSS}	±20	V		
Continuous Drain Current (Note 4) V _{GS} = 10V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	260 210	mA
Continuous Drain Current (Note 5) V _{GS} = 10V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I _D	400 310	mA

Thermal Characteristics

Characteristic	Symbol	Value	Units
Power Dissipation, @T _A = +25°C (Note 4)	P_{D}	430	mW
Thermal Resistance, Junction to Ambient $@T_A = +25^{\circ}C$ (Note 4)	$R_{ hetaJA}$	290	°C/W
Power Dissipation, @T _A = +25°C (Note 5)	P_{D}	840	mW
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 5)	$R_{\theta JSA}$	147	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage	BV _{DSS}	60	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	-	-	0.1	μΑ	V _{DS} = 60V, V _{GS} = 0V	
Gate-Body Leakage	I _{GSS}	-	-	±10	μΑ	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 6)	ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	V _{GS(th)}	1.2	-	2.0	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance	Б	-		3.0	Ω	$V_{GS} = 10V, I_D = 0.115A$	
Static Drain-Source On-Ivesistance	R _{DS} (ON)		-	4.0	32	$V_{GS} = 5V, I_D = 0.1115A$	
Forward Transfer Admittance	Y _{fs}	80	320	1	mS	$V_{DS} = 10V, I_D = 0.115A$	
Diode Forward Voltage	V_{SD}	-	0.7	1.2	V	$V_{GS} = 0V, I_S = 0.115A$	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	C _{iss}	-	25	-	pF		
Output Capacitance	Coss	-	4.7	-	pF	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$	
Reverse Transfer Capacitance	C _{rss}	-	2.5	-	pF	1	
Turn-On Delay Time	t _{D(on)}	-	3.27	-	ns		
Turn-On Rise Time	t _r	-	3.15	-	ns	$V_{DD} = 30V, V_{GEN} = 10V,$	
Turn-Off Delay Time	t _{D(off)}	-	12.025	-	ns	$R_{GEN} = 25\Omega, I_D = 0.115A$	
Turn-Off Fall Time	t _f	-	6.29	-	ns		

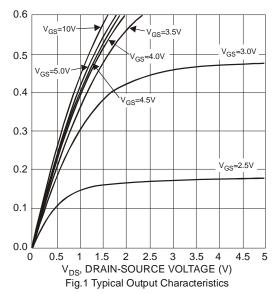
Notes:

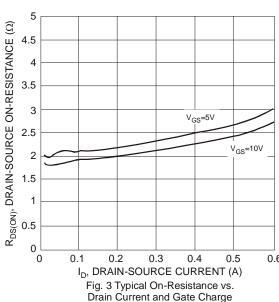
- 4. Device mounted on FR-4 PCB with minimum recommended pad layout, single-sided.
- Device mounted on 2" x 2" FR-4 PCB with high coverage 2oz. Copper, single-sided.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to production testing.

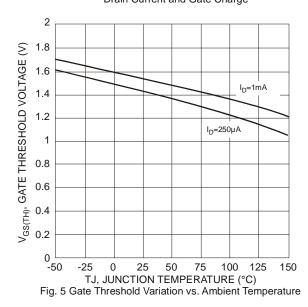
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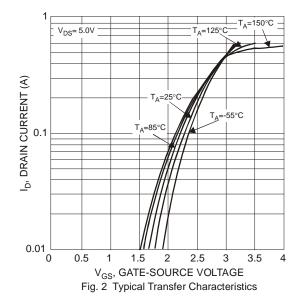
DODES

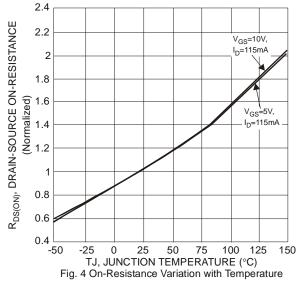
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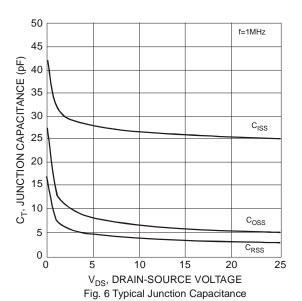








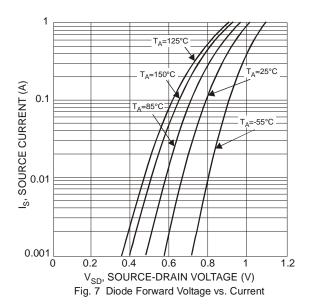




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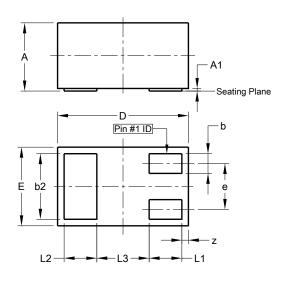


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Package Outline Dimensions

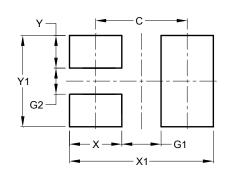
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



X1-DFN1006-3				
Dim	Min	Max	Тур	
Α	0.47	0.53	0.50	
A1	0.00	0.05	0.03	
b	0.10	0.20	0.15	
b2	0.45	0.55	0.50	
D	0.95	1.075	1.00	
Е	0.55	0.675	0.60	
е	-	-	0.35	
L1	0.20	0.30	0.25	
L2	0.20	0.30	0.25	
L3	-	-	0.40	
Z	0.02	0.08	0.05	
All Dimensions in mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	0.70
G1	0.30
G2	0.20
Х	0.40
X1	1.10
Y	0.25
Y1	0.70



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Document number: DS35545 Rev. 4 - 2

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